NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE4060K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

V_{DS} =40V,I_D =60A

 $R_{DS(ON)}$ <8.5m Ω @ V_{GS} =10V

 $R_{DS(ON)}$ <18m Ω @ V_{GS} =4.5V

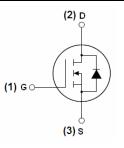
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-252-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE4060K	NCE4060K	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_c=25°Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	60	А
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	42	А
Pulsed Drain Current	I _{DM}	200	А
Maximum Power Dissipation	P _D	65	W
Derating factor		0.43	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	400	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$



Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{ heta JC}$	2.3	°C/W	l
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Electrical Characteristics (T_C=25 °C unless otherwise noted)

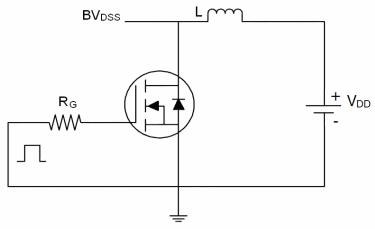
Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics	<u>.</u>						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	40	45	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μΑ	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)						•	
Gate Threshold Voltage	V _{GS(th)}	V_{DS} = V_{GS} , I_D =250 μ A	1.2	1.6	2.5	V	
Drain Course On Ctate Desistance		V _{GS} =10V, I _D =20A	-	7.3	8.5	m0	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =20A	15 18		18	- mΩ	
Forward Transconductance	g FS	V _{DS} =10V,I _D =20A	15	-	-	S	
Dynamic Characteristics (Note4)						•	
Input Capacitance	C _{lss}	V 00V/V 0V/	-	1800	-	PF	
Output Capacitance	C _{oss}	V_{DS} =20V, V_{GS} =0V, F=1.0MHz	-	280	-	PF	
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIHZ	-	190	-	PF	
Switching Characteristics (Note 4)						•	
Turn-on Delay Time	t _{d(on)}		-	6.4	-	nS	
Turn-on Rise Time	t _r	V_{DD} =20V, I_D =2A, R_L =1 Ω	-	17.2	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =3 Ω	-	29.6	-	nS	
Turn-Off Fall Time	t _f		-	16.8	-	nS	
Total Gate Charge	Qg	\/ 00\/ L 00A	-	29		nC	
Gate-Source Charge	Q_{gs}	V _{DS} =20V,I _D =20A,	-	4.5		nC	
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	6.4		nC	
Drain-Source Diode Characteristics						•	
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =10A	-		1.2	V	
Diode Forward Current (Note 2)	Is		-	-	60	Α	
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 20A	-	29	-	nS	
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	26	-	nC	
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD					

Notes:

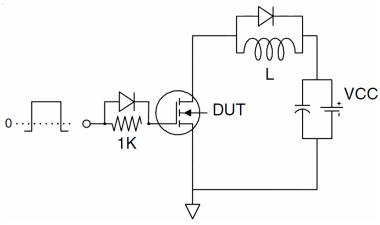
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- **4.** Guaranteed by design, not subject to production
- **5.** E_{AS} condition : Tj=25 $^{\circ}\text{C}$,V_DD=20V,V_G=10V,L=1mH,Rg=25 Ω ,

Test circuit

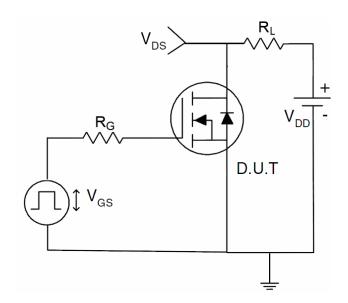
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

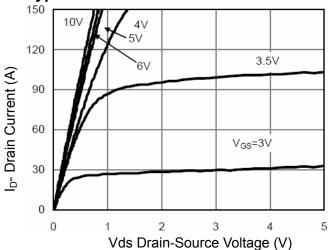


Figure 1 Output Characteristics

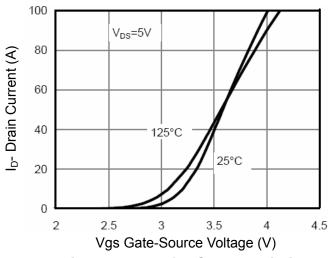


Figure 2 Transfer Characteristics

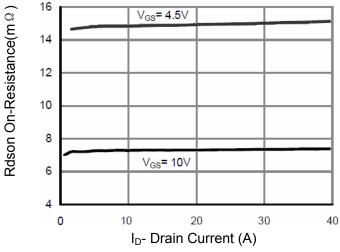


Figure 3 Rdson- Drain Current

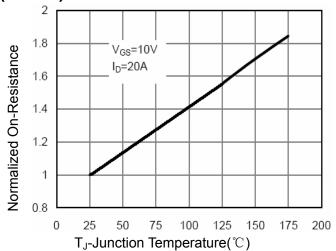


Figure 4 Rdson-JunctionTemperature

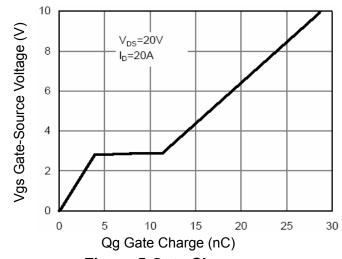


Figure 5 Gate Charge

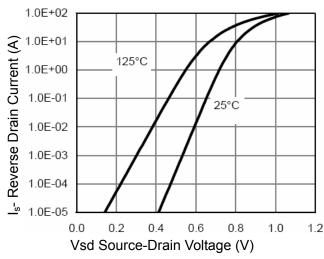
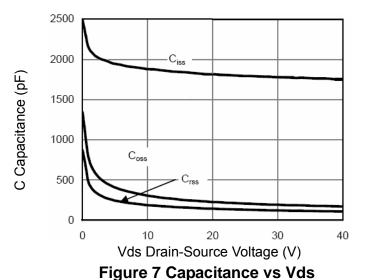
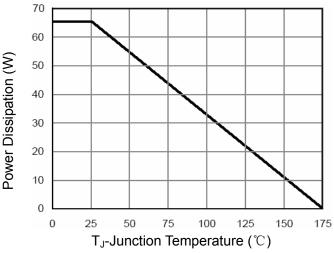


Figure 6 Source- Drain Diode Forward







1000.0

100.0

R_{DS(ON)}

100.0

R_{DS(ON)}

100 DC

100 us

100 us

1 ms

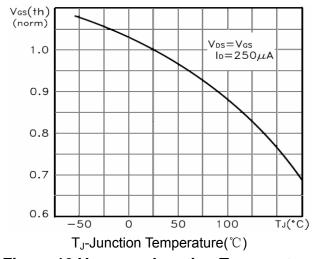
10ms

10ms

10ms

10ms

Figure 9 Power De-rating



Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area

10

100

0.1

0.01

Figure 10 V_{GS(th)} vs Junction Temperature

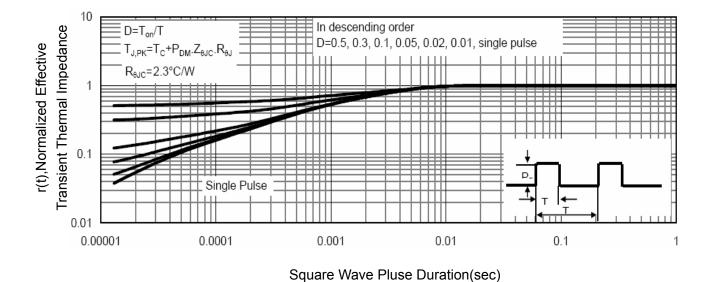
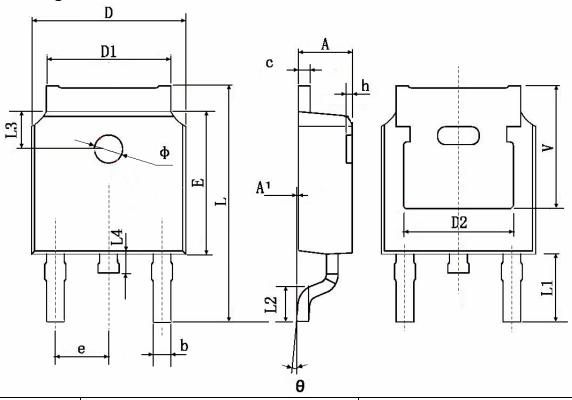


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252 Package Information



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830	TYP.	0.190 TYP.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900	TYP.	0.114	TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600	TYP.	0.063	TYP.	
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211 TYP.		



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